

<b>FORM PTO-1449</b>	Atty. Docket No.: B784.312-0001	Application No.: 10/017,734
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	First Named Inventor: Baowei KANG et al.	
	Filing Date: December 7, 2001	Group Art: <del>2826</del> 2823

## U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate
AA						
AB						
AC						
AD						
AE						
AF						

## FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Class	Sub Class	Translation Yes No
AG						
AH						
AI						

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<u>K.N.</u>	AJ	Hideo Iwamoto et al., "A New Punch-Through IGBT Having a New n-Buffer Layer", IEEE TRANSACTIONS ON INDUSTRY APPLICATIONS, Vol. 38, No. 1, January/February 2002, pp. 168-174.
<u>K.N.</u>	AK	T. Laska et al., "Optimizing the Vertical IGBT Structure - The NPT Concept as the Most Economic and Electrically Ideal Solution for a 1200V-IGBT", Proceedings of the ISPSD 1996, pp. 169-172.
<u>K.N.</u>	AL	Darryl Burns et al., "NPT-IGBT - Optimizing for Manufacturability", Proceedings of the ISPSD 1996, pp. 331-334.]
<u>K.N.</u>	AM	K. Mochizuki et al., "Examination of Punch Through IGBT(PT-IGBT) for High Voltage and High Current Applications", PROCEEDINGS of the ISPSD 1997, pp. 237-240.
<u>K.N.</u>	AN	G. Miller et al., "A New Concept for a Non Punch Through IGBT with MOSFET Like Switching Characteristics", 20th Annual IEEE Power Electronics Specialists Conference, 1989, pp. 21-25.
<u>K.N.</u>	AO	B. J. Baliga et al., "The Insulated Gate Rectifier (IGR): A New Power Switching Device", IEDM Technical Digest, 1982, pp. 264-267.

EXAMINER: Khien Nguyen DATE CONSIDERED: 03/22/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.